

N-Channel 200 V (D-S) MOSFET

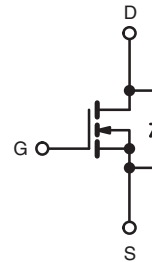
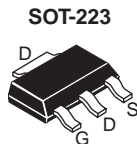
PRODUCT SUMMARY		
V _{DS} (V)	200	
R _{DS(on)} (Ω)	V _{GS} = 10 V	1.2
Q _g (Max.) (nC)	8.2	
Q _{gs} (nC)	1.8	
Q _{gd} (nC)	4.5	
Configuration	Single	

FEATURES

- Available in tape and reel
- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	A
		T _C = 100 °C	
Pulsed Drain Current ^a	I _{DM}	5.0	W/°C
Linear Derating Factor		0.025	
Linear Derating Factor (PCB Mount) ^e		0.017	
Single Pulse Avalanche Energy ^b	E _{AS}	50	mJ
Repetitive Avalanche Current ^a	I _{AR}	0.96	A
Repetitive Avalanche Energy ^a	E _{AR}	0.31	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	W
		T _A = 25 °C	
Peak Diode Recovery dV/dt ^c	dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature) ^d	for 10 s	300	

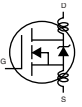

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 50 V, starting T_J = 25 °C, L = 81 mH, R_G = 25 Ω, I_{AS} = 0.96 A (see fig. 12).
- I_{SD} ≤ 3.3 A, dI/dt ≤ 70 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mount) ^a	R _{thJA}	-	-	40	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	-	-	60	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		200	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.30	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 0.58 A ^b	-	1.2	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = 50 V, I _D = 0.58 A		0.51	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	140	-	pF
Output Capacitance	C _{oss}			-	53	-	
Reverse Transfer Capacitance	C _{rss}			-	15	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 3.3 A, V _{DS} = 160 V, see fig. 6 and 13 ^b	-	-	8.2	nC
Gate-Source Charge	Q _{gs}			-	-	1.8	
Gate-Drain Charge	Q _{gd}			-	-	4.5	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 100 V, I _D = 3.3 A, R _g = 24 Ω, R _D = 30 Ω, see fig. 10 ^b		-	8.2	-	ns
Rise Time	t _r			-	17	-	
Turn-Off Delay Time	t _{d(off)}			-	14	-	
Fall Time	t _f			-	8.9	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.0	-	nH
Internal Source Inductance	L _S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	0.96	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	7.7	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 0.96 A, V _{GS} = 0 V ^b		-	-	2.0	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 3.3 A, dI/dt = 100 A/μs ^b		-	150	310	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.60	1.4	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

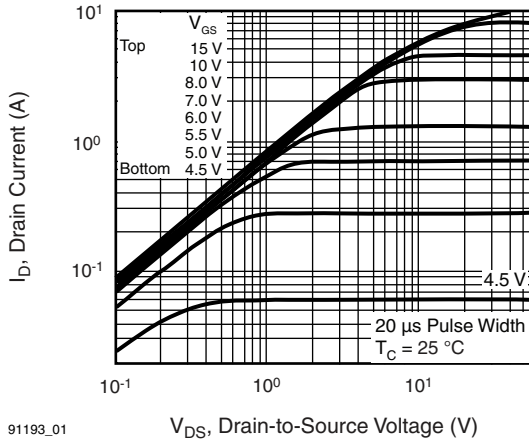


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

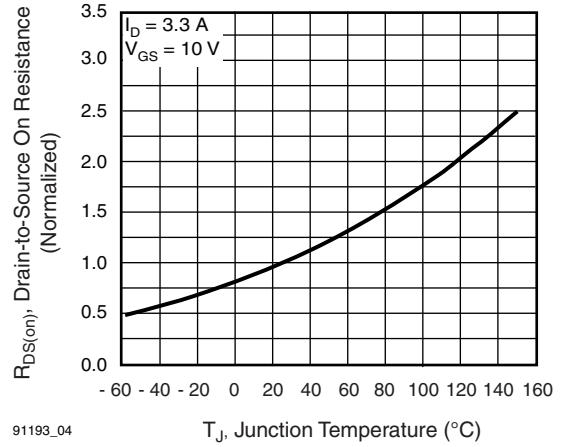


Fig. 4 - Normalized On-Resistance vs. Temperature

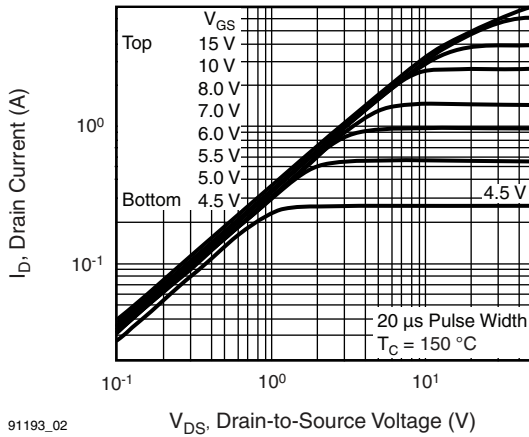


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

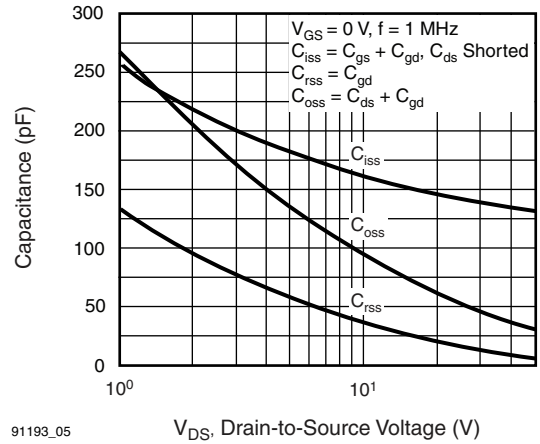


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

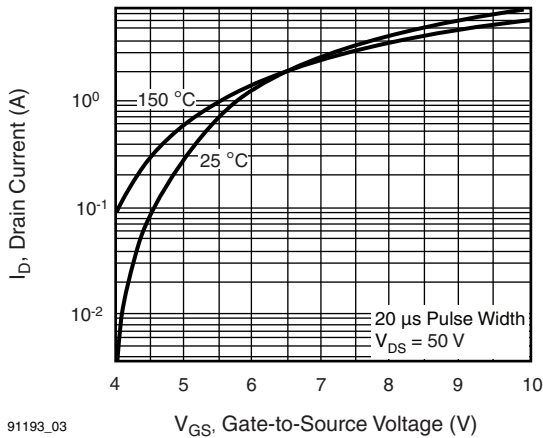


Fig. 3 - Typical Transfer Characteristics

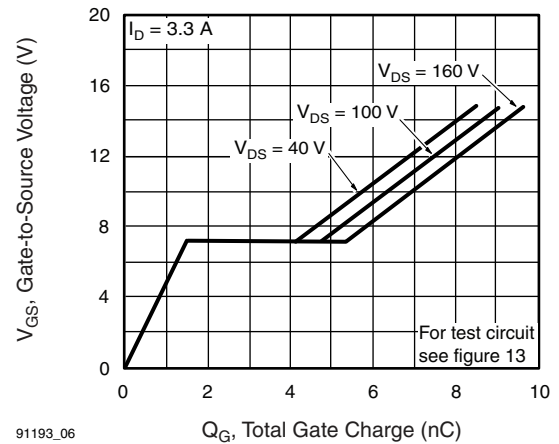
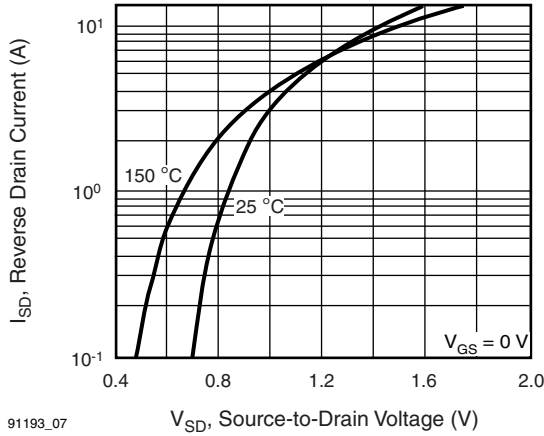
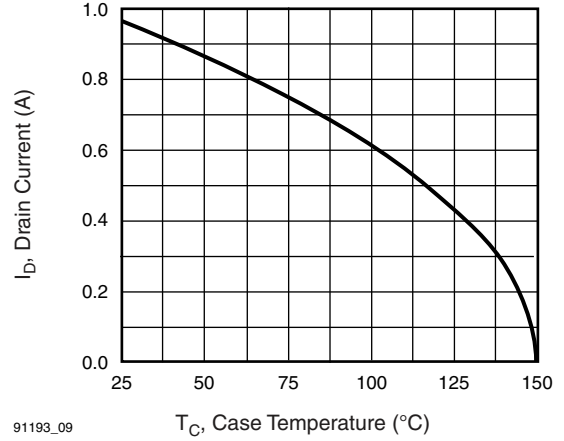


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



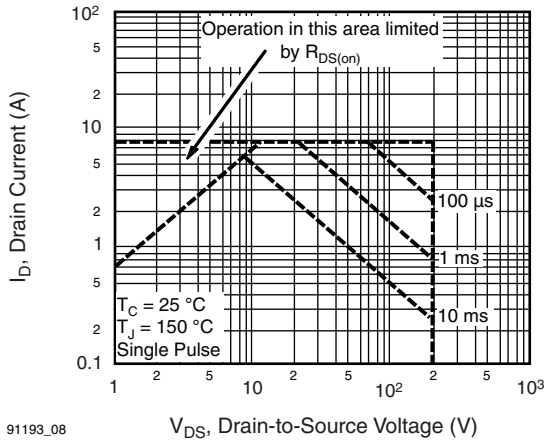
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91193_09

Fig. 9 - Maximum Drain Current vs. Case Temperature



91193_08

Fig. 8 - Maximum Safe Operating Area

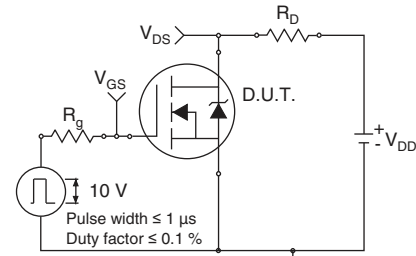


Fig. 10a - Switching Time Test Circuit

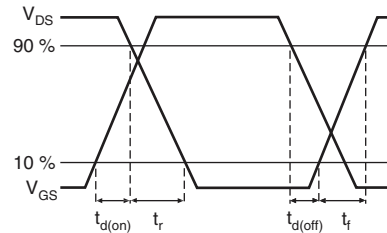
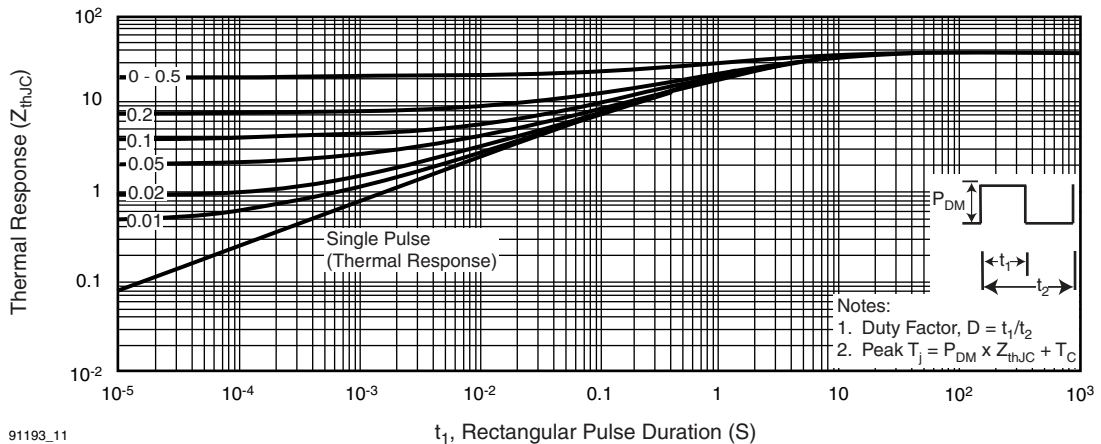


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

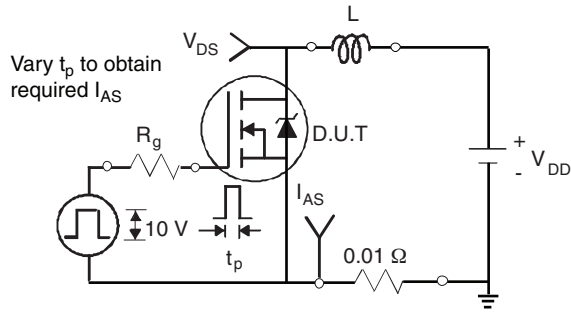


Fig. 12a - Unclamped Inductive Test Circuit

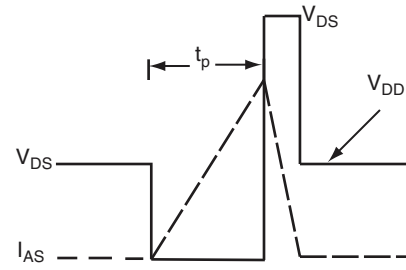


Fig. 12b - Unclamped Inductive Waveforms

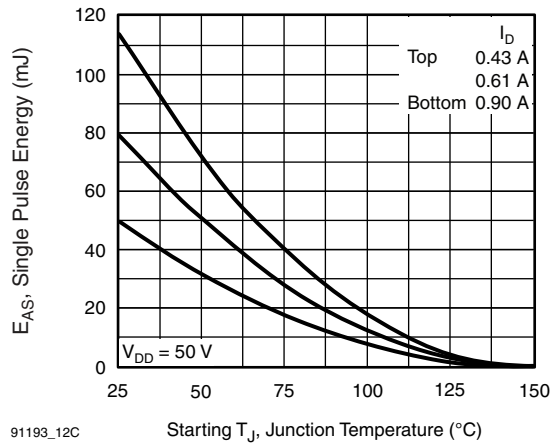


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

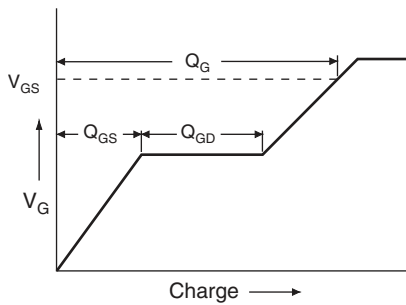


Fig. 13a - Basic Gate Charge Waveform

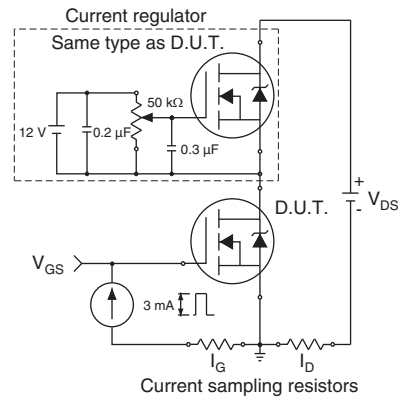
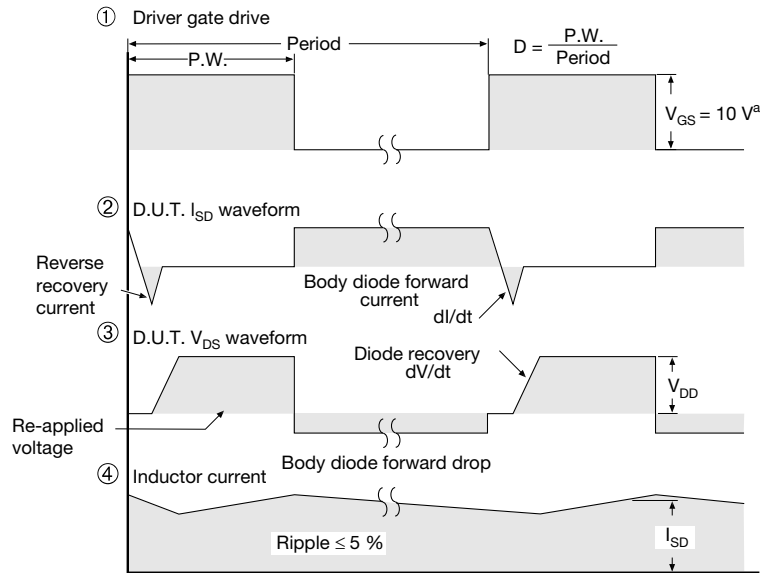
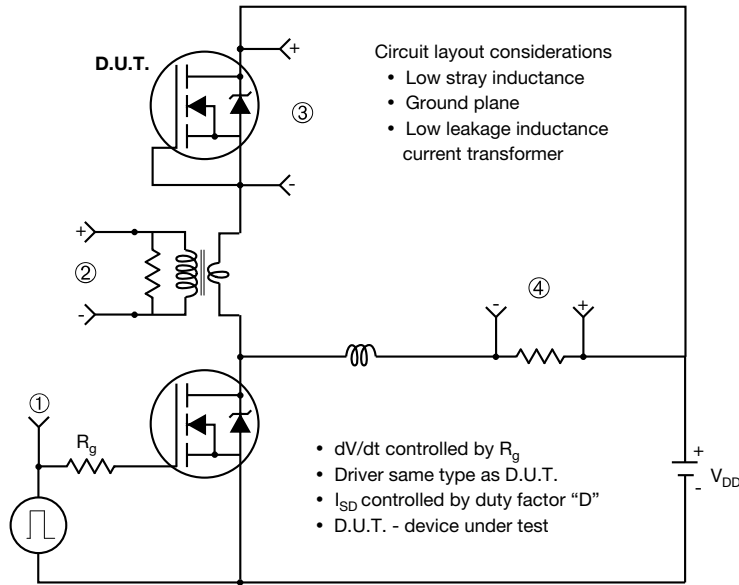


Fig. 13b - Gate Charge Test Circuit

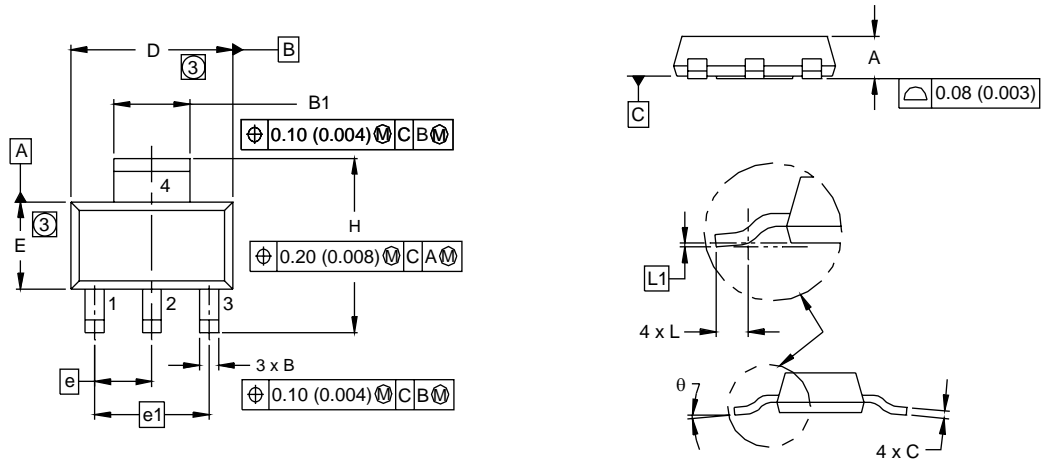
Peak Diode Recovery dV/dt Test Circuit



Note
a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

SOT-223



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
θ	-	10'	-	10'

ECN: S-82109-Rev. A, 15-Sep-08
DWG: 5969

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.

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